

IN THE SPECIFICATION**1. Changes To the Section Entitled "Brief Description of the Drawings"**

Please delete the description of FIGS. 1 and 2 in the Section entitled "Brief Description of the Drawings" (i.e., delete lines 10-15 at page 7) and replace them with a description of FIGS. 1-3 as recited below. A marked-up version of this substitution showing insertions and deletions is provided in Appendix A.

"FIG. 1 is a graph plotting current-voltage (I-V) values for an inventive FET device using pentacene as the semiconducting layer and bottom-contact micro-contact printed gold (Au) electrodes;

FIG. 2 is a graph plotting field-effect mobilities for inventive FET devices using copper phthalocyanine (CuPc) as the active semiconducting layer and top-contact micro-contact printed silver (Ag) electrodes; and

FIG. 3 illustrates an FET device of the invention. "

2. Changes To the Section Entitled "Summary of the Invention"

Please insert the following paragraph at page 6, line 20 after "deposited silsesquioxane precursor." and before "The silsesquioxane precursor":

"Referring to FIG. 3, in one embodiment, the invention is directed to an article comprising an organic FET comprising a gate electrode 1 on a substrate 2; an active dielectric layer 3 over the substrate 2; an active semiconducting layer 4 over the active dielectric layer, wherein the active dielectric layer comprises a low-temperature cured high-speed deposition product of at least silsesquioxane precursor; and a source electrode 5 and a drain electrode 6 in contact with the active semiconducting layer."

IN THE DRAWINGS

Please add new FIG. 3 in the application.

IN THE CLAIMS

Please replace claim 19 with amended claim 19 below. A marked-up version of claim 19 showing insertions and deletions is provided in Appendix B.

19. (amended) An article comprising an organic FET comprising:
a gate electrode on a substrate;
an active dielectric layer over the substrate;